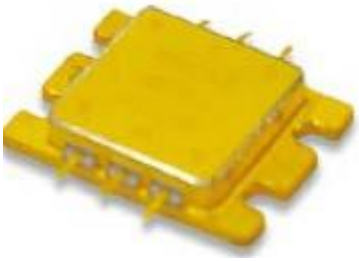
Performance

- Technology: 0.35um Power GaN HEMT&inter-matched
- Frequency: 2.3~2.5GHz
- Typical Pout : 53dBm
- Typical Gain: 12dB
- Bias: 45V/-5V
- Package: Metal Ceramic

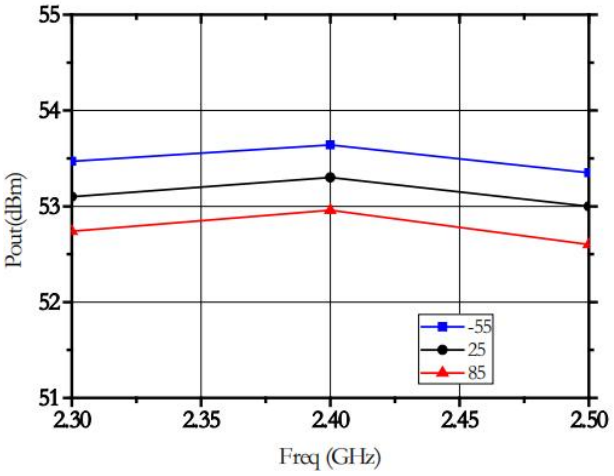


Electrical Specifications (T_A=25℃,PL=500us,D.C=12%)

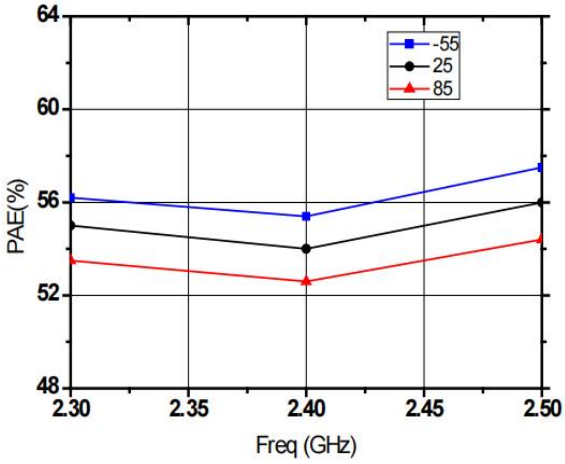
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	53	-	-	dBm
Gp	Power Gain	12	-	-	dB
ηadd	Power Added Efficiency		55	-	%
Rth	Thermal Resistance	-	-	0.22	℃/W

Test Curves

Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.

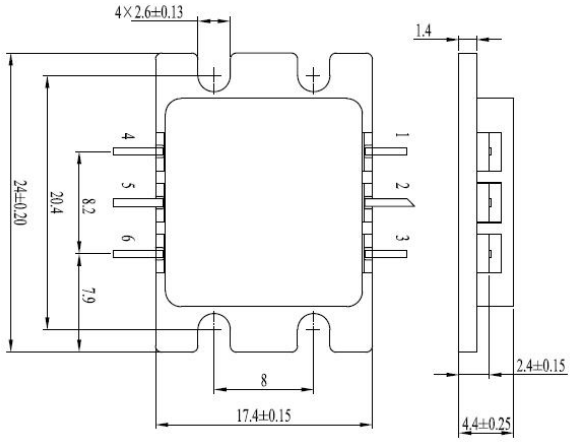


Absolute Max Ratings (T_A=25℃)

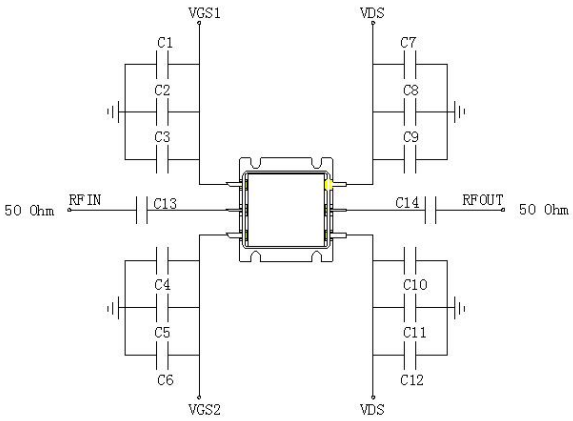
Symbol	Parameter	Value	Remark
Vd	Drain Voltage	80V	
Vg	Grid Voltage	-10V	
Tch	Channel Temperature	200℃	【1】
Tstg	Storage Temperature	-55~150℃	

【1】Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing



Application Circuit



Symbol	Value
C1/C4	100pF
C2/C5	1000pF
C3/C6	10uF
C7/C10	100pF
C8/C11	1000pF
C9/C12	47uF
C13	20pF
C14	20pF

Note:

(1) The input and output impedance values of this product are 50 ohms;

(2) The power-on sequence shall be in strict accordance with the sequence of applying negative power first and then positive power. When power-off, the leakage voltage shall be reduced first and then the grid voltage shall be reduced;

(3) Pay attention to heat dissipation during the use of this product. The higher the shell temperature is, the shorter the service life is. The service temperature should not be higher than 80 ℃;

(4) This product is an electrostatic sensitive device. It needs to pay attention to electrostatic protection during storage and use, and it needs to be grounded well during use;

(5) Power-up sequence VGS → VDS → RFIN;

(6) Power off sequence RFIN → VDS → VGS.